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CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage, in an envelope addressed to: Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450, on the below date:

Date: February 26, 2007 Name: Jasper W. Dockrey

Signature: *Jasper W. Dockrey*

BRINKS
HOFFER
GILSON
& LIONE

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Appln. of: Aspar et al.

Appln. No.: 10/534,199

Filed: May 6, 2005

For: METHOD FOR FORMING A BRITTLE
ZONE IN A SUBSTRATE BY CO-
IMPLANTATION

Examiner: TBA

Art Unit: 2812

Attorney Docket No: 9905/25

Mail Stop Amendment
Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

TRANSMITTAL

Sir:

Attached is/are:

☒ Transmittal Letter; Supplemental Information Disclosure Statement; Form PTO-1449 cited references B51-B107 and

☒ Return Receipt Postcard

Fee calculation:

☒ No additional fee is required.

☐ Small Entity.

☐ An extension fee in an amount of \$_____ for a _____-month extension of time under 37 C.F.R. § 1.136(a).

☐ A petition or processing fee in an amount of \$_____ under 37 C.F.R. § 1.17(____).

☐ An additional filing fee has been calculated as shown below:

					Small Entity		Not a Small Entity		
	Claims Remaining After Amendment		Highest No. Previously Paid For	Present Extra	Rate	Add'l Fee	or	Rate	Add'l Fee
Total		Minus			x \$25=			x \$50=	
Indep.		Minus			x 100=			x \$200=	
First Presentation of Multiple Dep. Claim					+ \$180=			+ \$360=	
					Total	\$		Total	\$

Fee payment

☐ A check in the amount of \$_____ is enclosed.

☐ Please charge Deposit Account No. 23-1925 in the amount of \$_____. A copy of this Transmittal is enclosed for this purpose.

☐ Payment by credit card in the amount of \$_____ (Form PTO-2038 is attached).

☒ The Director is hereby authorized to charge payment of any additional filing fees required under 37 CFR § 1.16 and any patent application processing fees under 37 CFR § 1.17 associated with this paper (including any extension fee required to ensure that this paper is timely filed), or to credit any overpayment, to Deposit Account No. 23-1925.

Respectfully submitted,

February 26, 2007

Date

Jasper W. Dockrey
Jasper W. Dockrey (Reg. No. 33,868)

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In re Appln. of: ASPAR ET AL.

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Attorney Docket No: 9905/25

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BS/

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

In accordance with the duty of disclosure under 37 C.F.R. §1.56 and §§1.97-1.98, and more particularly in accordance with 37 C.F.R. §1.97(b), Applicants hereby cite the following reference(s):

DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	NAME
4,028,149	6/7/1977	Deines et al.
4,254,590	3/10/1981	Eisele et al.
5,242,863	9/7/1993	Xiang-Zheng et al.
5,300,788	4/5/1994	Fan et al.
5,400,458	3/28/1995	Rambosek
5,405,802	4/11/1995	Yamagata et al.
5,559,043	9/24/1996	Bruei
5,811,348	9/22/1998	Matushita et al.
5,854,123	12/29/1998	Sato et al.
5,877,070	3/2/1999	Goesele et al.
5,909,627	6/1/1999	Egloff
5,920,764	7/6/1999	Hanson et al.
5,953,622	9/14/1999	Lee et al.
5,966,620	10/12/1999	Sakaguchi et al.
5,993,677	11/30/1999	Biasse et al.
5,994,207	11/30/1999	Henley et al.
6,013,563	1/11/2000	Henley et al.
6,048,411	4/11/2000	Henley et al.
6,054,370	4/25/2000	Doyle
6,071,795	6/6/2000	Cheung et al.
6,103,597	8/15/2000	Aspar et al.
6,103,599	8/15/2000	Henley et al.
6,127,199	10/3/2000	Inoue
6,146,979	11/14/2000	Henley et al.
6,150,239	11/21/2000	Goesele et al.

DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	NAME
6,190,998	2/20/2001	Bruel et al.
6,225,190	5/1/2001	Bruel et al.
6,225,192	5/1/2001	Aspar et al.
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6,513,564	2/4/2003	Bryan et al.
6,534,380	3/18/2003	Yamauchi et al.
6,593,212	7/15/2003	Kub et al.
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DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	COUNTRY
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EP 0 533 551 B1	3/9/2000	Europe
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DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	COUNTRY
FR 2 796 491	1/19/01	France
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Bruehl et al., [Vol. 99-1] Meeting Abstract No. 333, "Single-crystal semiconductor layer delamination and transfer through hydrogen implantation," <i>The 195th Meeting of The Electrochemical Society</i> , May 2-6, 1999, Seattle, Washington
Camperi-Ginestet et al., "Alignable Epitaxial Lift-off of GaAs Materials with Selective Deposition Using Polyimide Diaphragms", <i>IEEE Transactions Photonics Technology Letters</i> , Vol. 3, No. 12, December 1991, pp. 1123-1126
Cerofolini et al., "Ultradense Gas Bubbles in Hydrogen-or-Helium-Implanted (or Co-implanted) Silicon", <i>Materials Science and Engineering</i> , B71, 2000, pp. 196-202
Demeester, et al., "Epitaxial Lift-off and its Applications", <i>Semicond. Sci. Technol.</i> , Vol. 8, 1993, pp. 1124-1135
DiCioccio et al., "III-V layer transfer onto silicon and applications", <i>Phys. Stat. Sol. (a)</i> , Vol. 202, No. 4., 2005, pp. 509-515/DOI 10.1002/pssa.200460411
Feijoo et al., "Prestressing of Bonded Wafers", Vol. 92-7 1992 pp. 230-238
Feng et al., "Generalized Formula for Curvature Radius and Layer Stresses Caused by Thermal Strain in Semiconductor Multilayer Structures", <i>J. Appl. Phys.</i> , Vol. 54, No. 1, 1983, pp. 83-85
Hamaguchi, et al., "Novel LSI/SOI Wafer Fabrication Using Device Layer Transfer Technique" <i>Proc. IEDM</i> , 1985, pp. 688-691
Henttinen et al., "Mechanically induced Si Layer Transfer in Hydrogen-Implanted Si-Wafers", <i>American Institute of Physics</i> , Vol. 76, No. 17, April 2000, pp. 2370-2372
Kucheyev et al., "Ion implantation into GaN", <i>Materials Science and Engineering</i> , 33, 2001, pp. 51-107
Liu et al., "Ion implantation in GaN at liquid-nitrogen temperature: Structural characteristics and amorphization," <i>Physical Review B of The American Physical Society</i> , Vol. 57, No. 4, 1988, pp. 2530-2535

Moriceau et al., [Vol. 99-1] Meeting Abstract No. 405, "A New Characterization Process Used to Qualify SOI Films," <i>The 195th Meeting of The Electrochemical Society</i> , May 2-6, 1999, Seattle, Washington.
Pollentier et al., "Fabrication of High-Radiance LEDs by Epitaxial Lift-off" <i>SPIE</i> , Vol. 1361, 1990, pp. 1056-1062
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Timoshenko, S., "Analysis of Bi-Metal Thermostats", <i>J. Opt. Soc. Am.</i> , 11, 1925, pp. 233-256
Tong et al., "Low Temperature Si Layer Splitting", <i>Proceedings 1997 IEEE International SOI Conference</i> , Oct. 1997, pgs. 126-127
Wong et al., "Integration of GaN Thin Films with Dissimilar Substrate Materials by Pd-In Metal Bonding and Laser Lift-off", <i>Journal of Electronic Materials</i> , Vol. 28, No. 12, 1999, pp. 1409-1413
Yun et al., "Fractional Implantation Area Effects on Patterned Ion-Cut Silicon Layer Transfer," Dept. of Electrical Eng. And Computer Sciences, University of California, Berkeley, CA 94720, USA, 1999 IEEE International SOI Conference, Oct. 1999, pg. 129-30
Yun et al., "Thermal and Mechanical Separations of Silicon Layers from Hydrogen Pattern-Implanted Wafers," <i>Journal of Electronic Materials</i> , Vol. No. 36, No. 8 2001

Applicants are enclosing Form PTO-1449 (four sheets), along with a copy of each listed reference for which a copy is required under 37 C.F.R. §1.98(a)(2). As each of the listed references is in English, or an English abstract is provided, no further commentary is believed to be necessary, 37 C.F.R. §1.98(a)(3). Applicants respectfully request the Examiner's consideration of the above reference(s) and entry thereof into the record of this application.

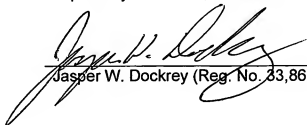
By submitting this Statement, Applicants are attempting to fully comply with the duty of candor and good faith mandated by 37 C.F.R. §1.56. As such, this Statement is not intended to constitute an admission that any of the enclosed references, or other information referred to therein, constitutes "prior art" or is otherwise "material to patentability," as that phrase is defined in 37 C.F.R. §1.56(a).

Applicants have calculated no fee to be due in connection with the filing of this Statement. However, the Director is authorized to charge any fee deficiency associated with the filing of this Statement to a deposit account, as authorized in the Transmittal accompanying this Statement.

Respectfully submitted,

February 26, 2007

Date



Jasper W. Dockrey (Reg. No. 33,868)



ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /BS/

FORM PTO-1449	SERIAL NO. 10/534,199	CASE NO. 9905/25
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE May 6, 2005	GROUP ART UNIT 2812
(use several sheets if necessary)	APPLICANT(S): Aspar et al.	

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER <small>Number-Kind Code (if known)</small>	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
	B1 4,028,149	6/7/1977	Deines et al.		
	B2 4,254,590	3/10/1981	Eisele et al.		
	B3 5,242,863	9/7/1993	Xiang-Zheng et al.		
	B4 5,300,788	4/5/1994	Fan et al.		
	B5 5,400,458	3/28/1995	Rambosek		
	B6 5,405,802	4/11/1995	Yamagata et al.		
	B7 5,559,043	9/24/1996	Bruel		
	B8 5,811,348	9/22/1998	Matushita et al.		
	B9 5,854,123	12/29/1998	Sato et al.		
	B10 5,877,070	3/2/1999	Goesele et al.		
	B11 5,909,627	6/1/1999	Egloff		
	B12 5,920,764	7/6/1999	Hanson et al.		
	B13 5,953,622	9/14/1999	Lee et al.		
	B14 5,966,620	10/12/1999	Sakaguchi et al.		
	B15 5,993,677	11/30/1999	Biasse et al.		
	B16 5,994,207	11/30/1999	Henley et al.		
	B17 6,013,563	1/11/2000	Henley et al.		
	B18 6,048,411	4/11/2000	Henley et al.		
	B19 6,054,370	4/25/2000	Doyle		
	B20 6,071,795	6/6/2000	Cheung et al.		
	B21 6,103,597	8/15/2000	Aspar et al.		
	B22 6,103,599	8/15/2000	Henley et al.		
	B23 6,127,199	10/3/2000	Inoue		
	B24 6,146,979	11/14/2000	Henley et al.		
	B25 6,150,239	11/21/2000	Goesele et al.		
	B26 6,190,998	2/20/2001	Bruel et al.		
	B27 6,225,190	5/1/2001	Bruel et al.		
	B28 6,225,192	5/1/2001	Aspar et al.		
	B29 6,271,101	8/7/2001	Fukunaga		
	B30 6,303,468	10/16/2001	Aspar et al.		
	B31 6,323,108	11/27/2001	Kub et al.		
	B32 6,323,109	11/27/2001	Okonogi		
	B33 6,346,458	2/12/2002	Bower		
	B34 6,362,077	3/26/2002	Aspar et al.		
	B35 6,513,564	2/4/2003	Bryan et al.		
	B36 6,534,380	3/18/2003	Yamauchi et al.		
	B37 6,593,212	7/15/2003	Kub et al.		
EXAMINER /Bradley Smith/	DATE CONSIDERED 02/16/2009				

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609;
Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	B38 6,607,969	8/19/2003	Kub et al.		
	B39 6,727,549	4/27/2004	Doyle		
	B40 6,756,286	6/29/2004	Moriceau et al.		
	B41 6,770,507	8/3/2004	Abe et al.		
	B42 6,946,365	9/20/2005	Aspar et al.		
	B43 2002/0025604	2/28/2002	Tiwari		
	B44 2002/0153563	10/24/2002	Ogura		
	B45 2002/0185684	12/12/2002	Campbell et al.		
	B46 2003/0077885	4/24/2003	Aspar et al.		
	B47 2003/0134489	7/17/2003	Schwarzenbach et al.		
	B48 2003/0162367	8/28/2003	Roche		
	B49 2003/0199105	10/23/2003	Kub et al.		
	B50 2004/0144487	7/29/2004	Martinez et al.		

FOREIGN PATENT DOCUMENTS

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	B51 EP 0 293 049 B1	9/29/1993	Europe		
	B52 EP 0 410 679 A1	1/30/1991	Europe		
	B53 EP 0 533 551 B1	3/9/2000	Europe		Abstract
	B54 EP 0 717 437 B1	4/24/2002	Europe		
	B55 EP 0 767 486 B1	1/2/2004	Europe		
	B56 EP 0 793 263 A2	9/3/1997	Europe		
	B57 EP 0 807 970 A1	11/19/1997	Europe		Abstract
	B58 EP 0 902 843 B1	3/29/2000	Europe		Abstract
	B59 EP 0 917 193 A1	5/19/1999	Europe		
	B60 EP 0 925 888 B1	11/10/2004	Europe		
	B61 EP 0 938 129 A1	8/25/1999	Europe		
	B62 EP 0 994 503 A1	4/19/2000	Europe		Abstract
	B63 EP 1 014 452 B1	5/3/2006	Europe		
	B64 EP 1 050 901 A2	11/8/2000	Europe		
	B65 FR 2 758 907 A1	7/31/1998	France		Abstract
	B66 FR 2 781 925 A1	2/4/2000	France		Abstract
	B67 FR 2 796 491	1/19/01	France		Abstract
	B68 FR 2 797 347	2/9/2001	France		Abstract
	B69 FR 2 809 867	12/7/2001	France		Abstract
	B70 FR 2 847 075 A1	5/14/2004	France		Abstract
	B71 JP 62265717	11/18/1987	Japan		Abstract

EXAMINER /Bradley Smith/	DATE CONSIDERED 02/16/2009
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	B72 JP 101004013	1/9/1989	Japan		Abstract
	B73 JP 07-254690	10/3/1995	Japan		Abstract
	B74 JP 7-302889	11/14/1995	Japan		Abstract
	B75 JP 09-213594	8/15/1997	Japan		Abstract
	B76 JP 09-307719	11/28/1997	Japan		Abstract
	B77 JP 11045862	2/16/1999	Japan		Abstract
	B78 JP 11074208	3/16/1999	Japan		Abstract
	B79 JP 11-145436	5/28/1999	Japan		Abstract
	B80 JP 11-233449	8/27/1999	Japan		Abstract
	B81 WO 99/08316	2/18/1999	WIPO		Abstract
	B82 WO 99/35674 A1	7/15/1999	WIPO		Abstract
	B83 WO 00/48238	8/17/2000	WIPO		Abstract
	B84 WO 01/11930A2	2/15/2001	WIPO		
	B85 WO 02/47156 A1	6/13/2002	WIPO		Abstract
	B86 WO 02/083387 A1	10/24/2002	WIPO		Abstract
	B87 WO 03/013815	2/20/2003	WIPO		Abstract
	B88 WO 04/044976	5/27/2004	WIPO		Abstract

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS <small>(Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.</small>
B89	Bruel et al., [Vol. 99-1] Meeting Abstract No. 333, "Single-crystal semiconductor layer delamination and transfer through hydrogen implantation," <i>The 195th Meeting of The Electrochemical Society</i> , May 2-6, 1999, Seattle, Washington
B90	Camperi-Ginestet et al., "Alignable Epitaxial Lift-off of GaAs Materials with Selective Deposition Using Polyimide Diaphragms", <i>IEEE Transactions Photonics Technology Letters</i> , Vol. 3, No. 12, December 1991, pp. 1123-1126
B91	Cerofolini et al. "Ultradense Gas Bubbles in Hydrogen-or-Helium-Implanted (or Co-implanted) Silicon", <i>Materials Science and Engineering</i> , B71, 2000, pp. 196-202
B92	Demeester, et al., "Epitaxial Lift-off and its Applications", <i>Semicond. Sci. Technol.</i> , Vol. 8, 1993, pp. 1124-1135
B93	DiCioccio et al., "III-V layer transfer onto silicon and applications", <i>Phys. Stat. Sol. (a)</i> , Vol. 202, No. 4., 2005, pp. 509-515/DOI 10.1002/pssa. 200460411
B94	Feijoo et al., "Prestressing of Bonded Wafers", Vol. 92-7 1992 pp. 230-238
B95	Feng et al., "Generalized Formula for Curvature Radius and Layer Stresses Caused by Thermal Strain in Semiconductor Multilayer Structures", <i>J. Appl. Phys.</i> , Vol. 54, No. 1, 1983, pp. 83-85
B96	Hamaguchi, et al., "Novel LSI/SOI Wafer Fabrication Using Device Layer Transfer Technique" <i>Proc. IEDM</i> , 1985, pp. 688-691
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EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.
B97	Henttinen et al. "Mechanically induced Si Layer Transfer in Hydrogen-Implanted Si-Wafers", <i>American Institute of Physics</i> , Vol. 76, No. 17, April 2000, pp. 2370-2372
B98	Kucheyev et al., "Ion implantation into GaN", <i>Materials Science and Engineering</i> , 33, 2001, pp. 51-107
B99	Liu et al., "Ion implantation in GaN at liquid-nitrogen temperature: Structural characteristics and amorphization," <i>Physical Review B of The American Physical Society</i> , Vol. 57, No. 4, 1988, pp. 2530-2535
B100	Moriceau et al., [Vol. 99-1] Meeting Abstract No. 405, "A New Characterization Process Used to Qualify SOI Films," <i>The 195th Meeting of The Electrochemical Society</i> , May 2-6, 1999, Seattle, Washington.
B101	Pollentier et al., "Fabrication of High-Radiance LEDs by Epitaxial Lift-off" <i>SPIE</i> , Vol. 1361, 1990, pp. 1056-1062
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B103	Timoshenko, S., "Analysis of Bi-Metal Thermostats", <i>J. Opt. Soc. Am.</i> , 11, 1925, pp. 233-256
B104	Tong et al., "Low Temperature Si Layer Splitting", <i>Proceedings 1997 IEEE International SOI Conference</i> , Oct. 1997, pgs. 126-127
B105	Wong et al., "Integration of GaN Thin Films with Dissimilar Substrate Materials by Pd-In Metal Bonding and Laser Lift-off", <i>Journal of Electronic Materials</i> , Vol. 28, No. 12, 1999, pp. 1409-1413
B106	Yun et al., "Fractional Implantation Area Effects on Patterned Ion-Cut Silicon Layer Transfer," Dept. of Electrical Eng. And Computer Sciences, University of California, Berkeley, CA 94720, USA, 1999 IEEE International SOI Conference, Oct. 1999, pg. 129-30
B107	Yun et al., "Thermal and Mechanical Separations of Silicon Layers from Hydrogen Pattern-Implanted Wafers," <i>Journal of Electronic Materials</i> , Vol. No. 36, No. 8 2001

EXAMINER /Bradley Smith/	DATE CONSIDERED 02/16/2009
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